

## NCE N-Channel Enhancement Mode Power MOSFET

### Description

The NCE6890 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

- $V_{DS} = 68V, I_D = 90A$   
 $R_{DS(ON)} < 7.5m\Omega @ V_{GS}=10V$  (Typ:6.5m $\Omega$ )
- Special process technology for high ESD capability
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

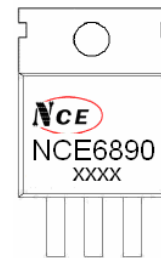
- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

**100%  $\Delta V_d$ s TESTED!**



Schematic diagram



Marking and pin assignment



TO-220-3L top view

### Package Marking and Ordering Information

| Device Marking | Device  | Device Package | Reel Size | Tape width | Quantity |
|----------------|---------|----------------|-----------|------------|----------|
| NCE6890        | NCE6890 | TO-220-3L      | -         | -          | -        |

### Absolute Maximum Ratings ( $T_C=25^\circ C$ unless otherwise noted)

| Parameter                                     | Symbol             | Limit    | Unit          |
|---|--------------------|----------|---------------|
| Drain-Source Voltage                          | $V_{DS}$           | 68       | V             |
| Gate-Source Voltage                           | $V_{GS}$           | $\pm 20$ | V             |
| Drain Current-Continuous                      | $I_D$              | 90       | A             |
| Drain Current-Continuous( $T_C=100^\circ C$ ) | $I_D(100^\circ C)$ | 63       | A             |
| Pulsed Drain Current                          | $I_{DM}$           | 320      | A             |
| Maximum Power Dissipation                     | $P_D$              | 130      | W             |
| Derating factor                               |                    | 0.86     | W/ $^\circ C$ |

| Parameter   | Symbol         | Limit      | Unit |
|---|----------------|------------|------|
| Single pulse avalanche energy <sup>(Note 5)</sup> | $E_{AS}$       | 380        | mJ   |
| Operating Junction and Storage Temperature Range  | $T_J, T_{STG}$ | -55 To 175 | °C   |

## Thermal Characteristic

|  |                 |      |      |
|--|-----------------|------|------|
| Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup> | $R_{\theta Jc}$ | 1.15 | °C/W |
|--|-----------------|------|------|

## Electrical Characteristics (TC=25°C unless otherwise noted)

| Parameter  | Symbol       | Condition   | Min | Typ  | Max  | Unit |
|--|--------------|---|-----|------|------|------|
| <b>Off Characteristics</b>                           |              |   |     |      |      |      |
| Drain-Source Breakdown Voltage                       | $BV_{DSS}$   | $V_{GS}=0V, I_D=250\mu A$   | 68  | 73   | -    | V    |
| Zero Gate Voltage Drain Current                      | $I_{DSS}$    | $V_{DS}=68V, V_{GS}=0V$   | -   | -    | 1    | μA   |
| Gate-Body Leakage Current                            | $I_{GSS}$    | $V_{GS}=\pm 20V, V_{DS}=0V$   | -   | -    | ±100 | nA   |
| <b>On Characteristics</b> <sup>(Note 3)</sup>        |              |   |     |      |      |      |
| Gate Threshold Voltage                               | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$   | 2   | 3    | 4    | V    |
| Drain-Source On-State Resistance                     | $R_{DS(ON)}$ | $V_{GS}=10V, I_D=30A$   | -   | 6.5  | 7.5  | mΩ   |
| Forward Transconductance                             | $g_{FS}$     | $V_{DS}=10V, I_D=20A$   | 20  | -    | -    | S    |
| <b>Dynamic Characteristics</b> <sup>(Note 4)</sup>   |              |   |     |      |      |      |
| Input Capacitance                                    | $C_{iss}$    | $V_{DS}=30V, V_{GS}=0V,$<br>$F=1.0MHz$                                    | -   | 3300 | -    | PF   |
| Output Capacitance                                   | $C_{oss}$    |   | -   | 450  | -    | PF   |
| Reverse Transfer Capacitance                         | $C_{rss}$    |   | -   | 170  | -    | PF   |
| <b>Switching Characteristics</b> <sup>(Note 4)</sup> |              |   |     |      |      |      |
| Turn-on Delay Time                                   | $t_{d(on)}$  | $V_{DD}=30V, I_D=30A$<br>$V_{GS}=10V, R_{GEN}=6\Omega$                    | -   | 15   | -    | nS   |
| Turn-on Rise Time                                    | $t_r$        |   | -   | 94   | -    | nS   |
| Turn-Off Delay Time                                  | $t_{d(off)}$ |   | -   | 46   | -    | nS   |
| Turn-Off Fall Time                                   | $t_f$        |   | -   | 32   | -    | nS   |
| Total Gate Charge                                    | $Q_g$        | $V_{DS}=30V, I_D=20A,$<br>$V_{GS}=10V$                                    | -   | 35   | -    | nC   |
| Gate-Source Charge                                   | $Q_{gs}$     |   | -   | 11   | -    | nC   |
| Gate-Drain Charge                                    | $Q_{gd}$     |   | -   | 9    | -    | nC   |
| <b>Drain-Source Diode Characteristics</b>            |              |   |     |      |      |      |
| Diode Forward Voltage <sup>(Note 3)</sup>            | $V_{SD}$     | $V_{GS}=0V, I_S=90A$  | -   | -    | 1.2  | V    |
| Diode Forward Current <sup>(Note 2)</sup>            | $I_S$        | -   | -   | -    | 90   | A    |
| Reverse Recovery Time                                | $t_{rr}$     | $T_J = 25^\circ C, I_F = 90A$<br>$di/dt = 100A/\mu s$ <sup>(Note 3)</sup> | -   | 78   | -    | nS   |
| Reverse Recovery Charge                              | $Q_{rr}$     |   | -   | 51   | -    | nC   |
| Forward Turn-On Time                                 | $t_{on}$     | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)      |     |      |      |      |

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5.  $E_{AS}$  condition:  $T_J=25^\circ C, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

**Test Circuit**

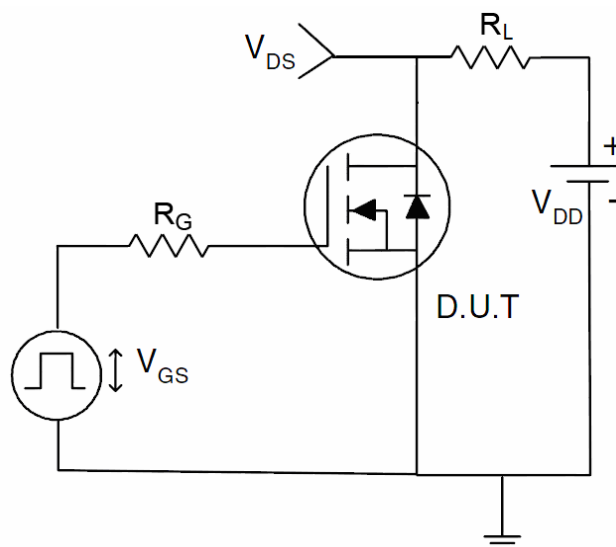
**1) E<sub>AS</sub> test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics (Curves)

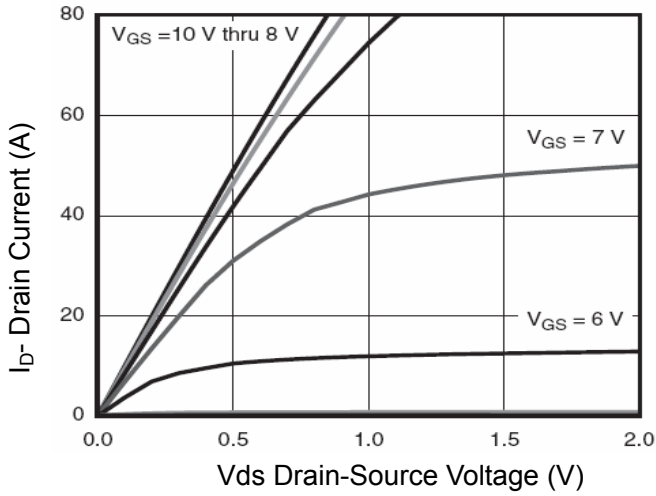


Figure 1 Output Characteristics

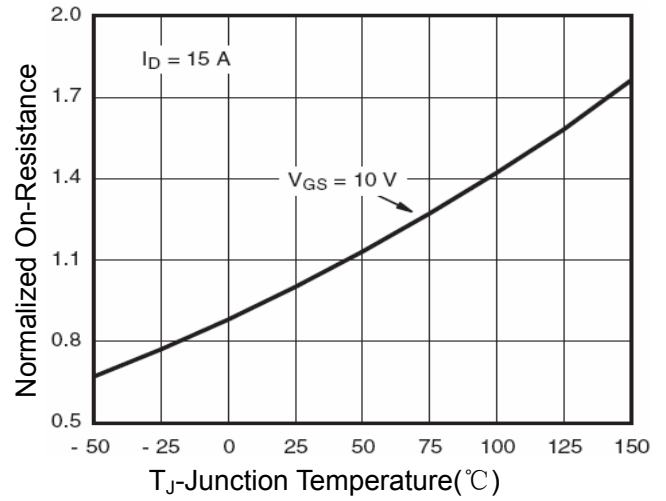


Figure 4 Rdson-Junction Temperature

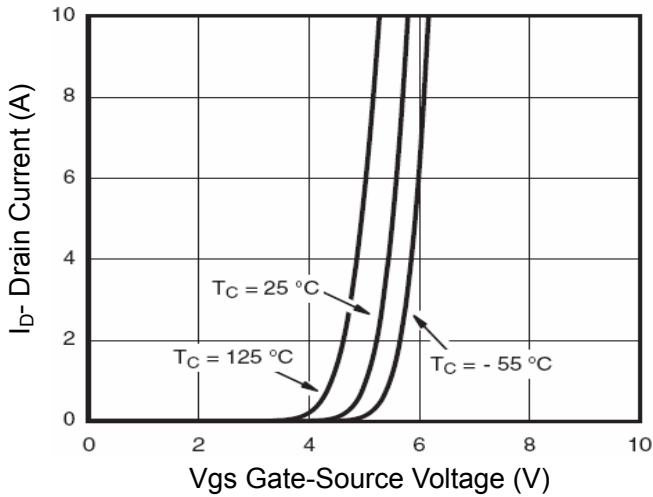


Figure 2 Transfer Characteristics

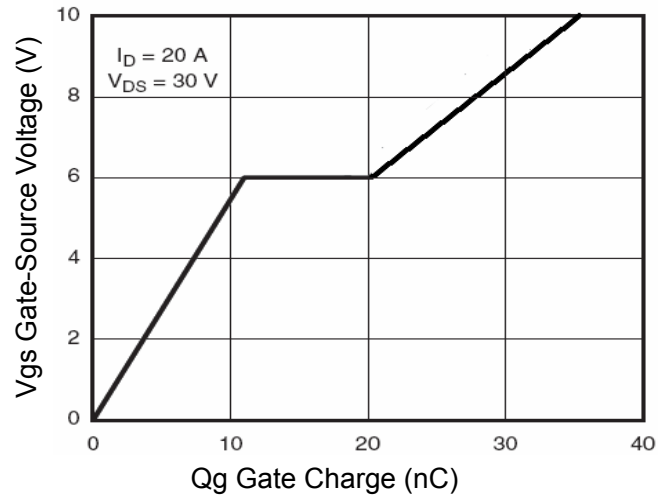


Figure 5 Gate Charge

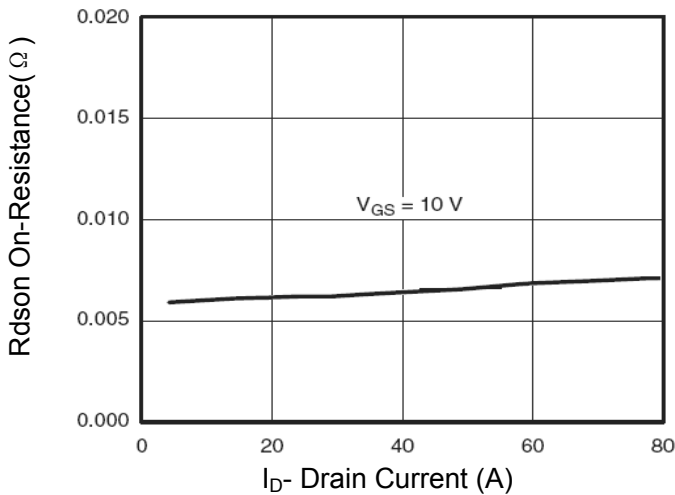


Figure 3 Rdson- Drain Current

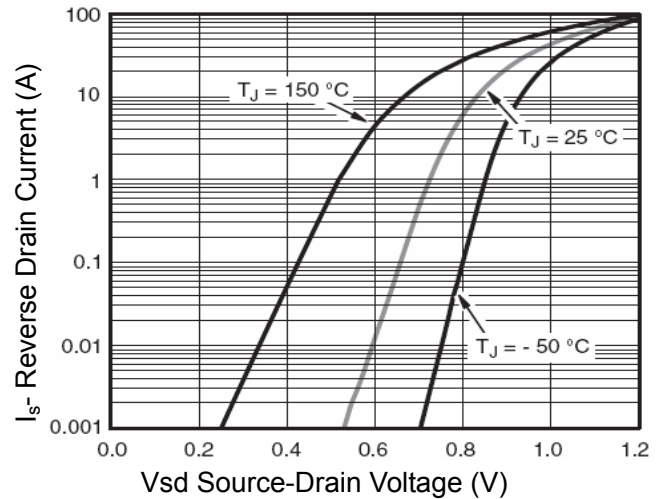


Figure 6 Source- Drain Diode Forward

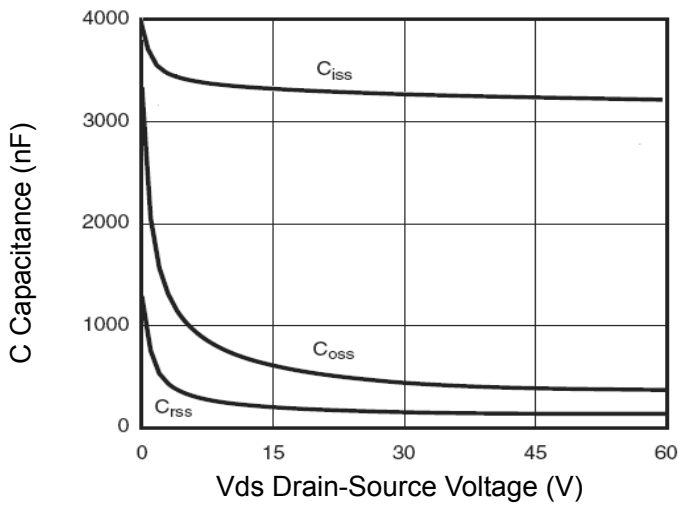


Figure 7 Capacitance vs Vds

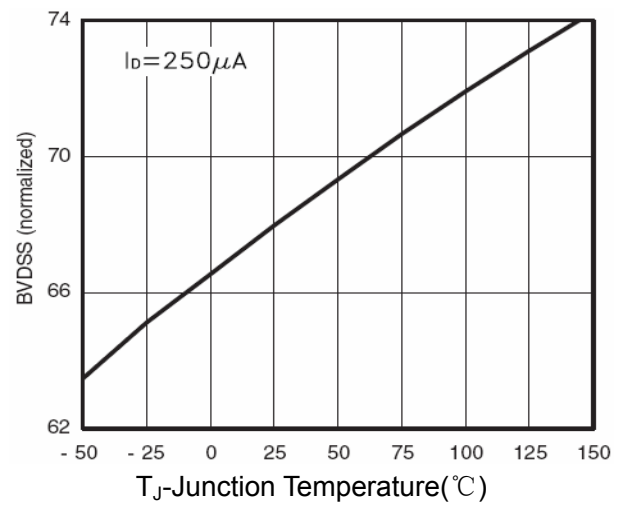


Figure 9  $BV_{DSS}$  vs Junction Temperature

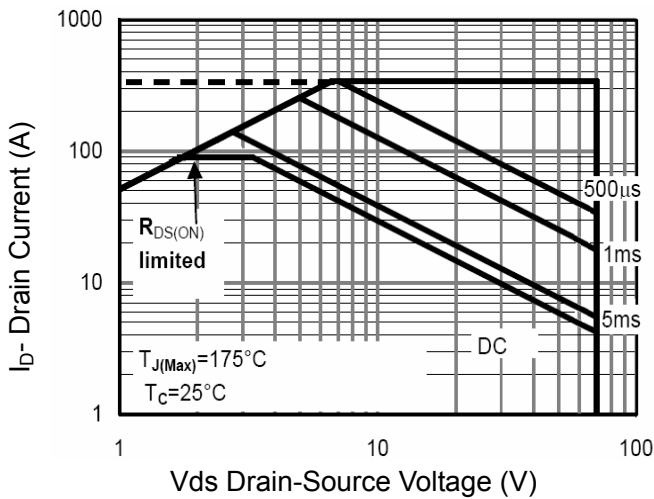


Figure 8 Safe Operation Area

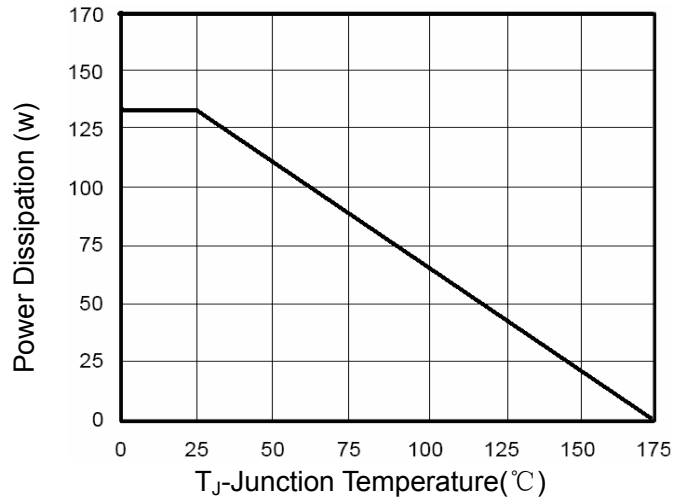


Figure 10 Power De-rating

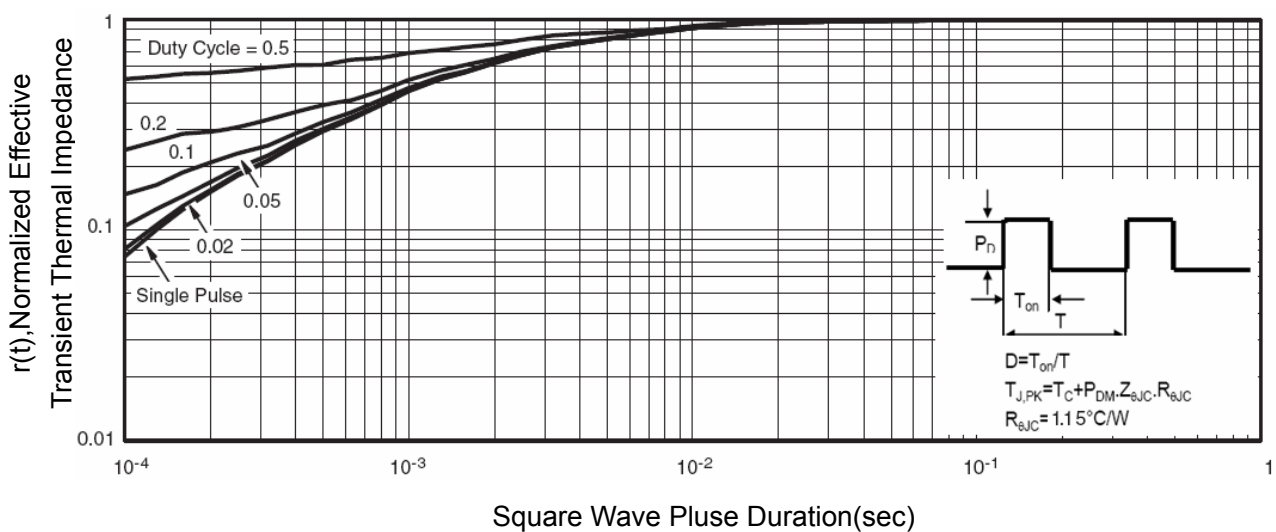
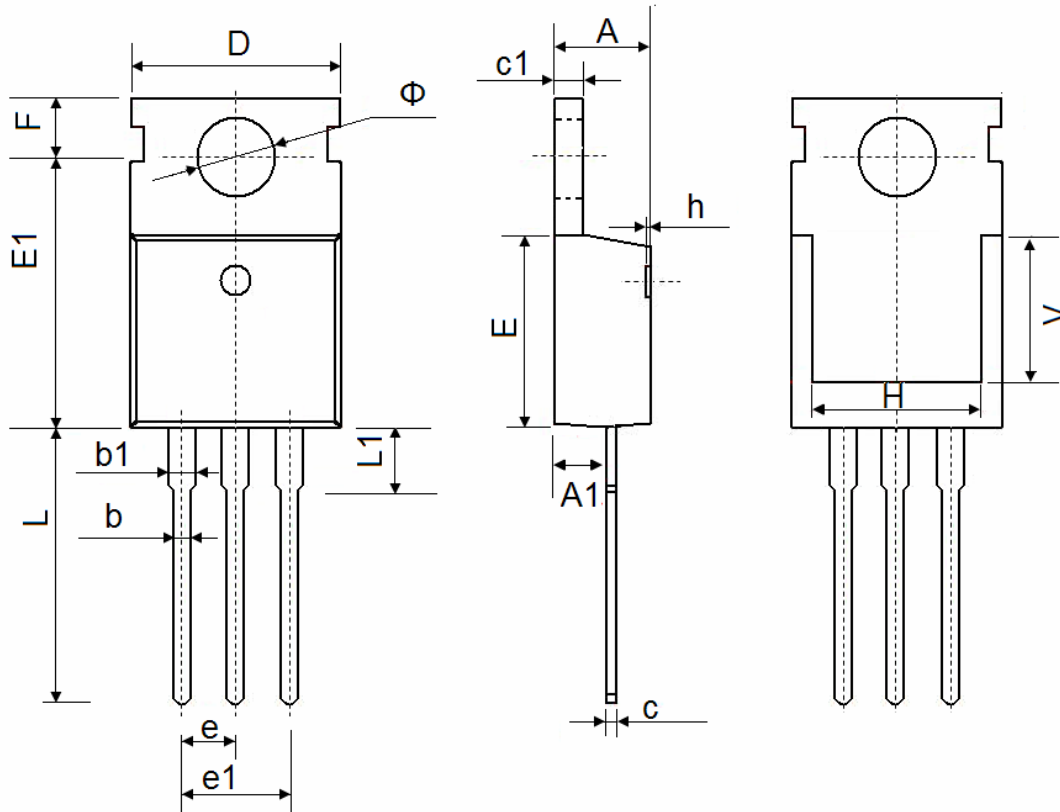


Figure 11 Normalized Maximum Transient Thermal Impedance

**TO-220-3L Package Information**


| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 4.400                     | 4.600  | 0.173                | 0.181 |
| A1     | 2.250                     | 2.550  | 0.089                | 0.100 |
| b      | 0.710                     | 0.910  | 0.028                | 0.036 |
| b1     | 1.170                     | 1.370  | 0.046                | 0.054 |
| c      | 0.330                     | 0.650  | 0.013                | 0.026 |
| c1     | 1.200                     | 1.400  | 0.047                | 0.055 |
| D      | 9.910                     | 10.250 | 0.390                | 0.404 |
| E      | 8.9500                    | 9.750  | 0.352                | 0.384 |
| E1     | 12.650                    | 12.950 | 0.498                | 0.510 |
| e      | 2.540 TYP.                |        | 0.100 TYP.           |       |
| e1     | 4.980                     | 5.180  | 0.196                | 0.204 |
| F      | 2.650                     | 2.950  | 0.104                | 0.116 |
| H      | 7.900                     | 8.100  | 0.311                | 0.319 |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| L      | 12.900                    | 13.400 | 0.508                | 0.528 |
| L1     | 2.850                     | 3.250  | 0.112                | 0.128 |
| V      | 7.500 REF.                |        | 0.295 REF.           |       |
| Φ      | 3.400                     | 3.800  | 0.134                | 0.150 |

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